Low-Power D-Type Transparent Latch with 3-State Output

The NL17SG373 MiniGate TM is an advanced high-speed CMOS D-Type Transparent Latch with 3-State Output in ultra-small footprint.

The NL17SG373 input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage.

This device is fully specified for partial power–down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: $t_{PD} = 2.4 \text{ ns (Typ)} @ V_{CC} = 3.0 \text{ V}, C_L = 15 \text{ pF}$
- Low Power Dissipation: $I_{CC} = 0.5 \mu A$ (Max) at $T_A = 25^{\circ}C$
- 5.5 V Overvoltage Tolerant (OVT) Input Pins
- Ultra-Small Packages
- These Devices are Pb-Free and are RoHS Compliant

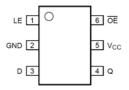


Figure 1. SC88 (Top View)

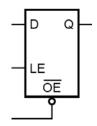


Figure 2. Logic Symbol



ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS



SC-88 DF SUFFIX CASE 419B



AG = Device Code

M = Date Code*

Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

Pin	Function
1	LE
2	GND
3	D
4	Q
5	V _{CC}
6	ŌĒ

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

FUNCTION TABLE

	Input			Output	
ŌĒ	LE	D	Internal Latch	Q	Operating Mode
L	Н	L	L	L	Enable and Read Register
L	Н	Н	Н	Н	(Transparent Mode)
L	L	Х	L	L	Latch and Read Register
L	L	Х	Н	Н	
Н	Х	Х	X	Z	Latch Register and Disable Output

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +5.5	V
V _{IN}	DC Input Voltage	-0.5 to +5.5	V
V _{OUT}	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current V _{OUT} < GND, V _{OUT} > V _{CC}	±50	mA
ΙO	DC Output Source/Sink Current	±20	mA
I _{CC}	DC Supply Current Per Supply Pin	±50	mA
I _{GND}	DC Ground Current per Ground Pin	±50	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	150	°C
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Mode (Note 2) Machine Model (Note 3)	> 3000 > 200	V
I _{LATCHUP}	Latchup Performance Above V _{CC} and Below GND at 125°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

- Tested to EIA / JESD22-A114-A.
 Tested to EIA / JESD22-A115-A.
- 4. Tested to EIA / JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	0.9	3.6	V
V _{IN}	Digital Input Voltage	0	3.6	V
V _{OUT}	Output Voltage Active Mode	0	V _{CC}	V
T _A	Operating Free–Air Temperature	- 55	+125	°C
Δt / ΔV	Input Transition Rise or Fail Rate V_{CC} = 3.3 V \pm 0.3 V	0	10	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

						T _A = 25°	С		\ = > +125°C	
Symbol	Parameter	С	onditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Uni
V _{IH}	High-Level			0.9	V _{CC}			V _{CC}		V
	Input Voltage			1.1 to 1.3	0.7 x V _{CC}			0.7 x V _{CC}		
				1.4 to 1.6	0.65 x V _{CC}			0.65 x V _{CC}		
				1.65 to 1.95	0.65 x V _{CC}			0.65 x V _{CC}		
				2.3 to 2.7	1.7			1.7		1
				3.0 to 3.6	2.0			2.0		
V _{IL}	Low-Level			0.9			GND		GND	V
	Input Voltage			1.1 to 1.3			0.3 x V _{CC}		0.3 x V _{CC}	
				1.4 to 1.6			0.35 x V _{CC}		0.35 x V _{CC}	
				1.65 to 1.95			0.35 x V _{CC}		0.35 x V _{CC}	
				2.3 to 2.7			0.7		0.7	
				3.0 to 3.6			0.8		0.8	
V_{OH}	Output V _{II}	V _{IN} =	I _{OH} = -20 μA	0.9	0.75			0.75		٧
		V _{IH} or V _{IL}	$I_{OH} = -0.3 \text{ mA}$	1.1 to 1.3	0.75 x V _{CC}			0.75 x V _{CC}		
			$I_{OH} = -1.7 \text{ mA}$	1.4 to 1.6	0.75 x V _{CC}			0.75 x V _{CC}		
			$I_{OH} = -3.0 \text{ mA}$	1.65 to 1.95	V _{CC} - 0.45			V _{CC} – 0.45		
			$I_{OH} = -4.0 \text{ mA}$	2.3 to 2.7	2.0			2.0		
			$I_{OH} = -8.0 \text{ mA}$	3.0 to 3.6	2.48			2.48		
V _{OL}	Low-Level	V _{IN} =	I _{OL} = 20 μA	0.9			0.1		0.1	V
	Output Voltage	V _{IH} or V _{IL}	I _{OL} = 0.3 mA	1.1 to 1.3			0.25 x V _{CC}		0.25 x V _{CC}	
			I _{OL} = 1.7 mA	1.4 to 1.6			0.25 x V _{CC}		0.25 x V _{CC}	
			I _{OL} = 3.0 mA	1.65 to 1.95			0.45		0.45	
			I _{OL} = 4.0 mA	2.3 to 2.7			0.4		0.4	
			I _{OL} = 8.0 mA	3.0 to 3.6			0.4		0.4	
I _{IN}	Input Leakage Current	0 ≤	$0 \le V_{IN} \le 3.6 \text{ V}$				±0.1		±0.5	μA
I _{CC}	Quiescent Supply Current	V _{IN} =	$V_{IN} = V_{CC}$ or GND				0.5		10	μA
l _{OZ}	3-State Output Leakage Current	V _{IN} V _{OU}	= V _{IH} or V _{IL} ; _T = 0 to 3.6 V	0.9 to 3.6			0.1		1	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ ns}$)

					T _A = 25 °C		-55°C to	∆ = o +125°C	
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay, D to Q	$C_L = 10 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	0.9	ı	15.3	-	_	_	ns
t _{PHL}	DioQ	KL = 1 IVIS2	1.1 to 1.3	-	6.3	12.3	1.0	14.4	
			1.4 to 1.6	-	4.4	8.1	1.0	9.4	
			1.65 to 1.95	-	3.6	6.2	0.5	6.7	
			2.3 to 2.7	_	2.6	3.9	0.5	4.4	
			3.0 to 3.6	_	2.1	3.1	0.5	3.7	
		C _L = 15 pF,	0.9	_	17.7	_	-	-	ns
		$R_L^2 = 1 M\Omega$	1.1 to 1.3	-	7.1	13.6	1.0	15.6	
			1.4 to 1.6	-	5.0	9.2	1.0	10.4	
			1.65 to 1.95	-	4.1	6.9	1.0	7.1	
			2.3 to 2.7	-	2.9	4.4	0.5	5.0	
			3.0 to 3.6	-	2.4	3.4	0.5	3.9	
		$C_L = 30 \text{ pF},$	0.9	-	29	-	-	-	ns
	$R_L = 1 \text{ M}\Omega$	1.1 to 1.3	-	9.3	17.3	1.0	21.2		
		1.4 to 1.6	-	6.4	11.6	1.0	12.6	1	
			1.65 to 1.95	-	5.3	9.1	1.0	9.6	
			2.3 to 2.7	-	4	5.7	1.0	6.1	
			3.0 to 3.6	-	3.3	4.4	1.0	4.8	
t _{PLH} ,	Propagation Delay,	$C_L = 10 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	0.9	-	15.3	-	-	-	ns
t _{PHL}	LE to Q		1.1 to 1.3	_	6.3	12.3	1.0	14.4	
			1.4 to 1.6	_	4.4	8.1	1.0	9.4	
			1.65 to 1.95	-	3.6	6.2	0.5	6.7	
			2.3 to 2.7	_	2.6	3.9	0.5	4.4	
			3.0 to 3.6	-	2.1	3.1	0.5	3.7	1
		$C_L = 15 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	0.9	-	17.7	-	-	_	ns
		$R_L = 1 M\Omega$	1.1 to 1.3	-	7.1	13.6	1.0	15.6	1
			1.4 to 1.6	-	5.0	9.2	1.0	10.4	1
			1.65 to 1.95	-	4.1	6.9	1.0	7.1	
			2.3 to 2.7	_	2.9	4.4	0.5	5.0	
			3.0 to 3.6	_	2.4	3.4	0.5	3.9	
		$C_L = 30 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	0.9	_	29	_	-	_	ns
		$R_L = 1 M\Omega$	1.1 to 1.3	_	9.3	17.3	1.0	21.2	1
			1.4 to 1.6	_	6.4	11.6	1.0	12.6	1
			1.65 to 1.95	-	5.3	9.1	1.0	9.6	
			2.3 to 2.7	-	4	5.7	1.0	6.1	1
			3.0 to 3.6	_	3.3	4.4	1.0	4.8	1

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ ns}$)

					T _A = 25 °C		-55°C to	գ = o +125°C	
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit
			0.9	_	18.9	_	-	-	
			1.1 to 1.3	_	6.0	10.2	1	10.6	
		C = 10 pF	1.4 to 1.6	_	4.5	6.5	1	7.0	
		$C_L = 10 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	3.9	5.4	1	5.8	ns
			2.3 to 2.7	_	2.5	3.5	1	3.8	1
			3.0 to 3.6	_	2.1	2.7	1	3	1
			0.9	_	22	-	-	-	
			1.1 to 1.3	_	6.8	11.6	1	12.1	1
		0 15 5	1.4 to 1.6	_	5.1	7.2	1	7.9	1
t _{PZH} , t _{PZL}	Output Enable Time, OE to Q	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	4.4	6.1	1	6.5	ns
			2.3 to 2.7	_	2.9	3.9	1	4.2	1
			3.0 to 3.6	_	2.3	3	1	3.3	1
			0.9	_	31.8	-	-	-	
			1.1 to 1.3	_	9.1	15.7	1	16.2	1
			1.4 to 1.6	-	6.7	9.5	1	10.5	ns
		$C_L = 30 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	5.7	7.9	1	8.6	
			2.3 to 2.7	_	3.8	5	1	5.5	1
			3.0 to 3.6	_	2.9	3.8	1	4.2	1
		$C_L = 10 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	0.9	_	11.3	_	_	-	
			1.1 to 1.3	_	5.3	8.3	1	8.4	1
			1.4 to 1.6	_	4.1	5.8	1	6.1	ns
			1.65 to 1.95	_	4.2	5.7	1	5.9	
			2.3 to 2.7	_	3.0	4	1	4.2	
			3.0 to 3.6	_	3.4	4.7	1	5	1
			0.9	_	11	_	_	_	
			1.1 to 1.3	_	5.8	8.2	1	11	1
			1.4 to 1.6	_	3.9	5.9	1	8	1
t _{PHZ} , t _{PLZ}	Output Disable Time, _{OE} to Q	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65 to 1.95	_	4.5	6.6	1	7.4	ns
			2.3 to 2.7	_	3.2	4.3	1	5.1	1
			3.0 to 3.6	_	4.8	6.2	1	6.7	1
			0.9	_	17.7	_	_	_	†
			1.1 to 1.3	_	9.9	15.7	1	16	1
			1.4 to 1.6	_	7.7	10.8	1	11.6	1
		$C_L = 30 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	6	12.9	1	12.9	ns
			2.3 to 2.7	_	5	9.1	1	9.5	1
			3.0 to 3.6	_	4	12.5	1	13	1

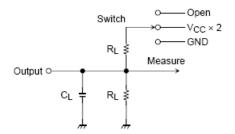
AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

					T _A = 25 °C			T _A = -55°C to +125°C		
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit	
C _{IN}	Input Capacitance		0 to 3.6		1.5	-	-	-	pF	
Co	Output Capacit- ance	V _O = GND	0		3	ı	-	ı	pF	
			0.9	ı	1.6	ı		ı		
			1.1 to 1.3	-	1.7	-		_		
	Power dissipation	f =10 MHz;	1.4 to 1.6	-	1.8	-		_		
C _{PD} Capacitance (Note 5)	pacitance $V_I = GND$ to	1.65 to 1.95	-	1.9	-		-	pF		
]	2.3 to 2.7	-	2.2	-		_		
			3.0 to 3.6	_	2.7	_		_		

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption: P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

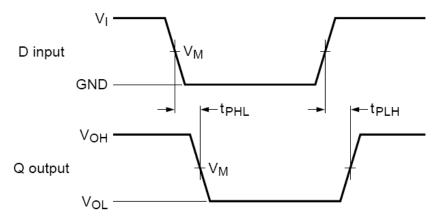
TIMING REQUIREMENTS (Input $t_r = t_f = 3.0 \text{ ns}$; $C_L = 5 \text{ pF}$, 10 pF, 15 pF and 20 pF)

					T _A = 25 °C	;	T _A -55°C to	= +125°C		
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit	
				0.9	_	4.0	_	-	-	
			1.1 to 1.3	_	0.7	-	2.1	-		
			1.4 to 1.6	_	0.5	-	1.3	-		
t _W Pulse Width, LE	High	1.65 to 1.95	-	0.4	-	1.0	_	ns		
			2.3 to 2.7	-	0.3	-	0.8	-		
			3.0 to 3.6	_	0.2	_	0.8	-	1	
	Set-Up Time, D to LE High or Low		0.9	_	2.1	_	-	-		
		High or Low	1.1 to 1.3	_	0.5	_	2.7	-	ns	
			1.4 to 1.6	_	0.3	_	1.5	-		
t _{SU}			1.65 to 1.95	-	0.3	-	1.2	_		
			2.3 to 2.7	_	0.2	_	0.9	-		
			3.0 to 3.6	_	0.2	_	0.7	-		
			0.9	_	-2.8	-	-	-		
			1.1 to 1.3	_	-0.7	-	-0.1	-		
			1.4 to 1.6	_	-0.4	_	-0.1	-	1	
t _H	Hold Time D to LE	High or Low	1.65 to 1.95	-	-0.4	-	0	_	ns	
			2.3 to 2.7	-	-0.3	-	0.2	-	1	
			3.0 to 3.6	-	-0.4	-	0.3	-		



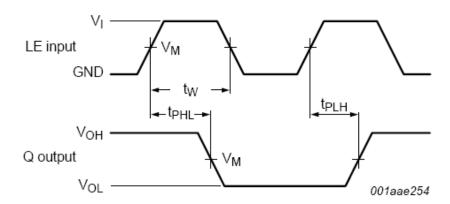
Characteristics	Switch
t _{pLH} , t _{pHL}	Open
t _{pLZ} , t _{pZL}	V _{CC} × 2
t _{pHZ} , t _{pZH}	GND

Figure 3. Test Circuit



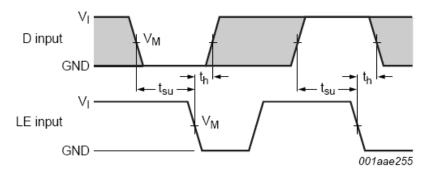
Logic levels: $V_{\mbox{OL}}$ and $V_{\mbox{OH}}$ are typical output voltage levels that occur with the output load.

Figure 4. t_{PLH} , t_{PHL} Waveforms (D to Q)



Logic levels: $V_{\mbox{OL}}$ and $V_{\mbox{OH}}$ are typical output voltage levels that occur with the output load.

Figure 5. t_{PLH} , t_{PHL} , t_{W} Waveforms (LE to Q)

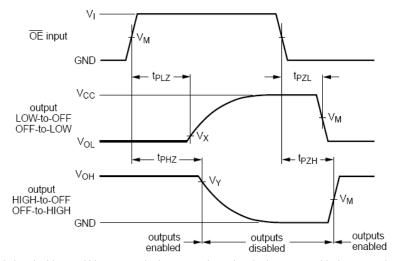


Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Figure 6. t_{SU}, t_H Waveforms (D to LE)

MEASUREMENT POINTS FOR FIGURES 4, 5 AND 6

Supply Voltage		Input	Output	
V _{CC}	V _M	V _I	$t_r = t_f$	V _M
0.9 V to 3.6 V	0.5 x V _{CC}	V _{CC}	≤ 3.0 ns	0.5 x V _{CC}



Logic levels: $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are typical output voltage levels that occur with the output load.

Figure 7. t_{PLZ} , t_{PHZ} , t_{PZH} , t_{PZL} Waveforms ($\overline{\text{OE}}$ to Q)

MEASUREMENT POINTS FOR FIGURE 7

Supply Voltage		Input			Output			
V _{CC}	V _M	VI	$t_r = t_f$	V _M	V _X	V _Y		
0.9 V	0.5 x V _{CC}	V _{CC}	≤ 3.0 ns	0.5 x V _{CC}	V _{OL} + 0.1 V	V _{OH} – 0.1 V		
1.1 V to 1.3 V	0.5 x V _{CC}	V _{CC}	≤ 3.0 ns	0.5 x V _{CC}	V _{OL} + 0.1 V	V _{OH} – 0.1 V		
1.4 V to 1.6 V	0.5 x V _{CC}	V _{CC}	≤ 3.0 ns	0.5 x V _{CC}	V _{OL} + 0.1 V	V _{OH} – 0.1 V		
1.65 V to 1.95 V	0.5 x V _{CC}	V _{CC}	≤ 3.0 ns	0.5 x V _{CC}	V _{OL} + 0.15 V	V _{OH} – 0.15 V		
2.3 V to 2.7 V	0.5 x V _{CC}	V _{CC}	≤ 3.0 ns	0.5 x V _{CC}	V _{OL} + 0.15 V	V _{OH} – 0.15 V		
3.0 V to 3.6 V	0.5 x V _{CC}	V _{CC}	≤ 3.0 ns	0.5 x V _{CC}	V _{OL} + 0.3 V	V _{OH} – 0.3 V		

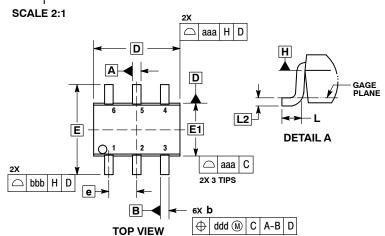
ORDERING INFORMATION

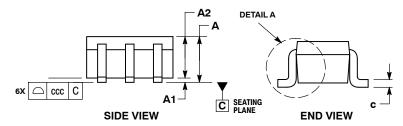
Device	Package	Shipping [†]
NL17SG373DFT2G	SC-88 / SOT-363 / SC-70-6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

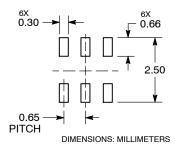
SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE Y**

DATE 11 DEC 2012





RECOMMENDED



SOLDERING FOOTPRINT*

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS
- CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.

- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC		0.026 BSC			
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code* = Pb-Free Package

(Note: Microdot may be in either location)

- *Date Code orientation and/or position may vary depending upon manufacturing location.
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42985B	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-88/SC70-6/SOT-363		PAGE 1 OF 2	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

DOCUMENT NUMBER:	98ASB42985B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-88/SC70-6/SOT-363		PAGE 2 OF 2	

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative